

N-Channel JFETs

J308	SST308	U309
J309	SST309	U310
J310	SST310	

PRODUCT SUMMARY				
Part Number	$V_{GS(off)}$ (V)	$V_{(BR)GSS}$ Min (V)	g_{fs} Min (mS)	I_{DSS} Min (mA)
J308	-1 to -6.5	-25	8	12
J309	-1 to -4	-25	10	12
J310	-2 to -6.5	-25	8	24
SST308	-1 to -6.5	-25	8	12
SST309	-1 to -4	-25	10	12
SST310	-2 to -6.5	-25	8	24
U309	-1 to -4	-25	10	12
U310	-2.5 to -6	-25	10	24

FEATURES

- Excellent High Frequency Gain: Gps 11.5 dB @ 450 MHz
- Very Low Noise: 2.7 dB @ 450 MHz
- Very Low Distortion
- High ac/dc Switch Off-Isolation

BENEFITS

- Wideband High Gain
- Very High System Sensitivity
- High Quality of Amplification
- High-Speed Switching Capability
- High Low-Level Signal Amplification

APPLICATIONS

- High-Frequency Amplifier/Mixer
- Oscillator
- Sample-and-Hold
- Very Low Capacitance Switches

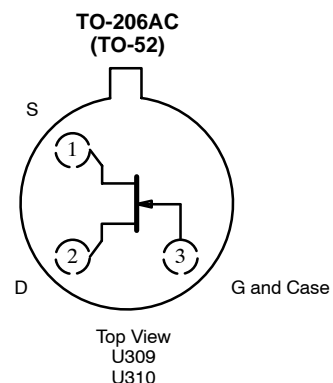
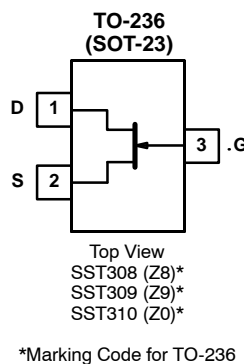
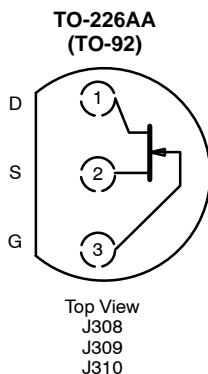
DESCRIPTION

The J/SST/U308 series offers superb amplification characteristics. Of special interest is its high-frequency performance. Even at 450 MHz, this series offers high power gain at low noise.

Low-cost J series TO-226AA (TO-92) packaging supports automated assembly with tape-and-reel options. The SST series TO-236 (SOT-23) package provides surface-mount capabilities

and is available with tape-and-reel options. The U series hermetically-sealed TO-206AC (TO-52) package supports full military processing. (See Military and Packaging Information for further details.)

For similar dual products packaged in the TO-78, see the U430/431 data sheet.



For applications information see AN104.

ABSOLUTE MAXIMUM RATINGS

Gate-Drain, Gate-Source Voltage	-25 V
Gate Current :	(J/SST Prefixes)	10 mA
	(U Prefix)	20 mA
Lead Temperature (1/16" from case for 10 sec.)	300°C
Storage Temperature :	(J/SST Prefixes)	-55 to 150°C
	(U Prefix)	-65 to 175°C

Operating Junction Temperature	-55 to 150°C
Power Dissipation :	(J/SST Prefixes) ^a	350 mW
	(U Prefix) ^b	500 mW

Notes

- Derate 2.8 mW/°C above 25°C
- Derate 4 mW/°C above 25°C

SPECIFICATIONS FOR J/SST308, J/SST309 AND J/SST310 (T_A = 25°C UNLESS NOTED)

Parameter	Symbol	Test Conditions	Typ ^a	Limits						Unit
				J/SST308		J/SST309		J/SST310		
				Min	Max	Min	Max	Min	Max	
Static										
Gate-Source Breakdown Voltage	V _{(BR)GSS}	I _G = -1 μA, V _{DS} = 0 V	-35	-25		-25		-25		V
Gate-Source Cutoff Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 nA		-1	-6.5	-1	-4	-2	-6.5	V
Saturation Drain Current ^b	I _{DSS}	V _{DS} = 10 V, V _{GS} = 0 V		12	60	12	30	24	60	mA
Gate Reverse Current	I _{GSS}	V _{GS} = -15 V, V _{DS} = 0 V	-0.002		-1		-1		-1	nA
		T _A = 125°C	-0.001		-1		-1		-1	μA
Gate Operating Current	I _G	V _{DG} = 9 V, I _D = 10 mA	-15							pA
Drain-Source On-Resistance	r _{DS(on)}	V _{GS} = 0 V, I _D = 1 mA	35							Ω
Gate-Source Forward Voltage	V _{GS(F)}	I _G = 10 mA V _{DS} = 0 V	J	0.7		1		1		V
Dynamic										
Common-Source Forward Transconductance	g _{fs}	V _{DS} = 10 V, I _D = 10 mA f = 1 kHz	14	8		10		8		mS
Common-Source Output Conductance	g _{os}		110		250		250		250	μS
Common-Source Input Capacitance	C _{iss}	V _{DS} = 10 V V _{GS} = -10 V f = 1 MHz	J	4		5		5		pF
			SST	4						
Common-Source Reverse Transfer Capacitance	C _{rss}		J	1.9		2.5		2.5		
			SST	1.9						
Equivalent Input Noise Voltage	e _n	V _{DS} = 10 V, I _D = 10 mA f = 100 Hz	6							nV/ √Hz
High Frequency										
Common-Gate Forward Transconductance	g _{fg}	V _{DS} = 10 V I _D = 10 mA	f = 105 MHz	14						mS
			f = 450 MHz	13						
Common-Gate Output Conductance	g _{og}		f = 105 MHz	0.16						
			f = 450 MHz	0.55						
Common-Gate Power Gain ^c	G _{pg}		f = 105 MHz	16					dB	
			f = 450 MHz	11.5						
Noise Figure	NF		f = 105 MHz	1.5						
			f = 450 MHz	2.7						

Notes

- Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- Pulse test: PW ≤ 300 μs duty cycle ≤ 3%.
- Gain (G_{pg}) measured at optimum input noise match.

NZB



SPECIFICATIONS FOR U309 AND U310 (T _A = 25 °C UNLESS NOTED)								
Parameter	Symbol	Test Conditions	Typ ^a	Limits				Unit
				U309		U310		
				Min	Max	Min	Max	
Static								
Gate-Source Breakdown Voltage	V _{(BR)GSS}	I _G = -1 μA, V _{DS} = 0 V	-35	-25		-25		V
Gate-Source Cutoff Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 nA		-1	-4	-2.5	-6	V
Saturation Drain Current ^b	I _{DSS}	V _{DS} = 10 V, V _{GS} = 0 V		12	30	24	60	mA
Gate Reverse Current	I _{GSS}	V _{GS} = -15 V, V _{DS} = 0 V	-0.002		-0.15		-0.15	nA
		T _A = 125 °C	-0.001		-0.15		-0.15	μA
Gate Operating Current	I _G	V _{DG} = 9 V, I _D = 10 mA	-15					pA
Drain-Source On-Resistance	r _{DS(on)}	V _{GS} = 0 V, I _D = 1 mA	35					Ω
Gate-Source Forward Voltage	V _{GS(F)}	I _G = 10 mA, V _{DS} = 0 V	0.7		1		1	V
Dynamic								
Common-Source Forward Transconductance	g _{fs}	V _{DS} = 10 V, I _D = 10 mA f = 1 kHz	14	10		10		mS
Common-Source Output Conductance	g _{os}		110		250		250	μS
Common-Source Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = -10 V f = 1 MHz	4		5		5	pF
Common-Source Reverse Transfer Capacitance	C _{rss}		1.9		2.5		2.5	
Equivalent Input Noise Voltage	e _n	V _{DS} = 10 V, I _D = 10 mA f = 100 Hz	6					nV/ √Hz
High Frequency								
Common-Gate Forward Transconductance	g _{fg}	V _{DS} = 10 V I _D = 10 mA	f = 105 MHz	14				mS
			f = 450 MHz	13				
Common-Gate Output Conductance	g _{og}		f = 105 MHz	0.16				
			f = 450 MHz	0.55				
Common-Gate Power Gain ^{c, d}	G _{pg}		f = 105 MHz	16	14		14	dB
			f = 450 MHz	11.5	10		10	
Noise Figure ^d	NF		f = 105 MHz	1.5		2	2	
			f = 450 MHz	2.7		3.5	3.5	

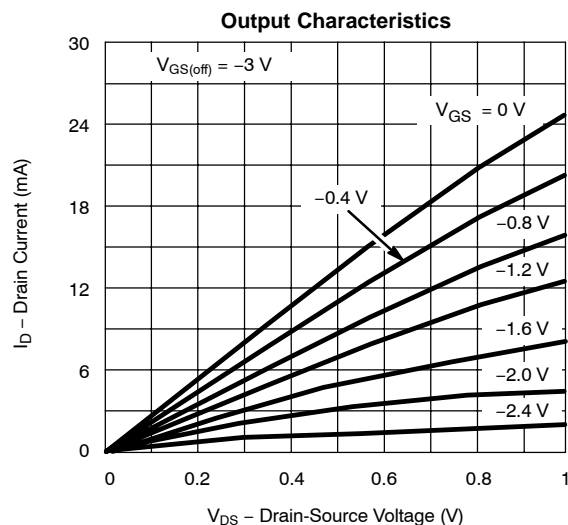
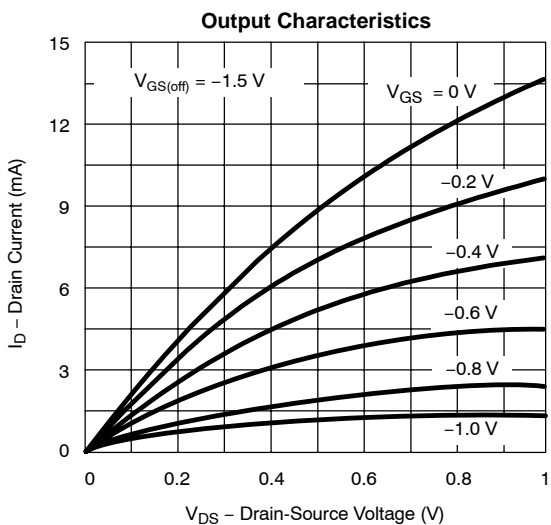
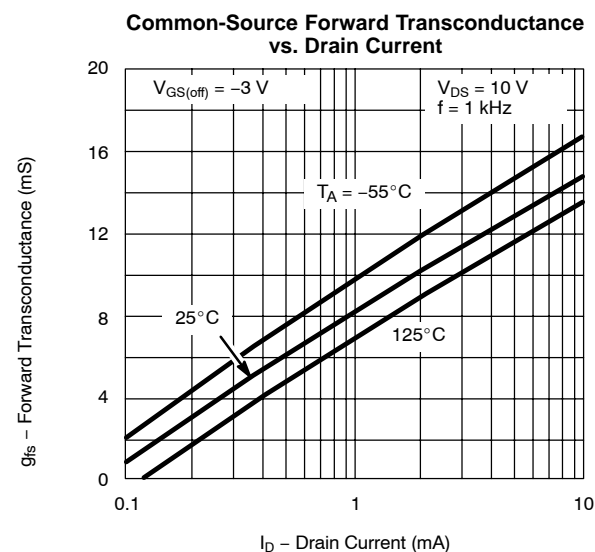
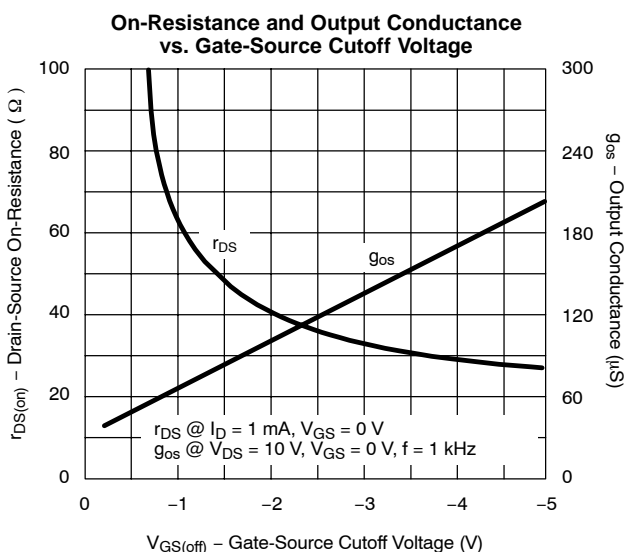
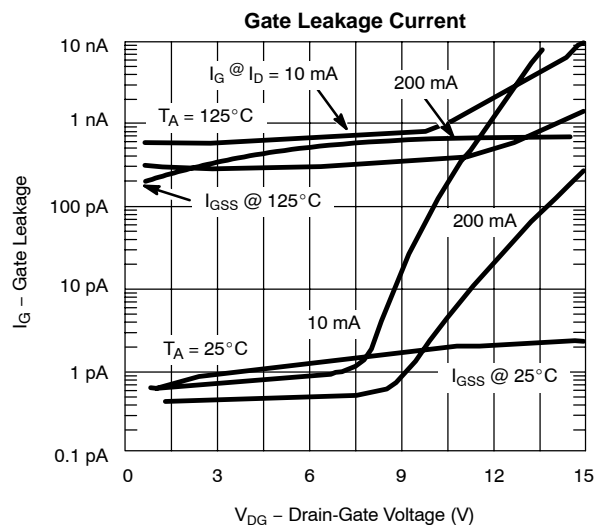
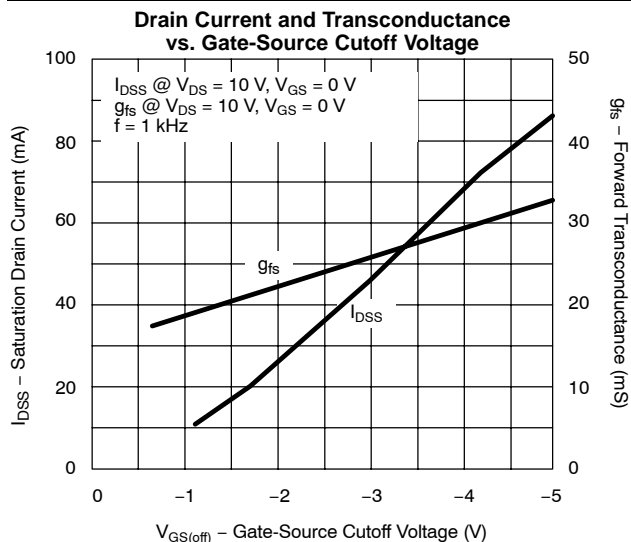
Notes

- a. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- b. Pulse test: PW ≤ 300 μs duty cycle ≤ 3%.
- c. Gain (G_{pg}) measured at optimum input noise match.
- d. Not a production test.

NZB

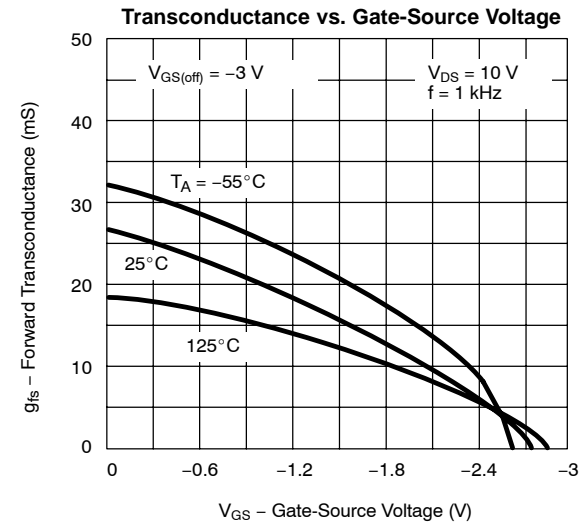
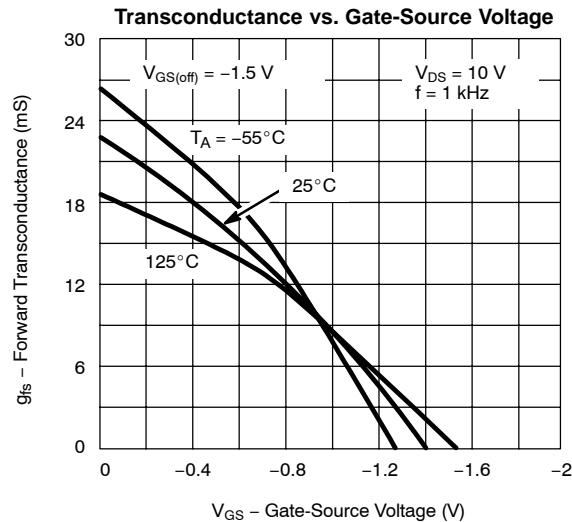
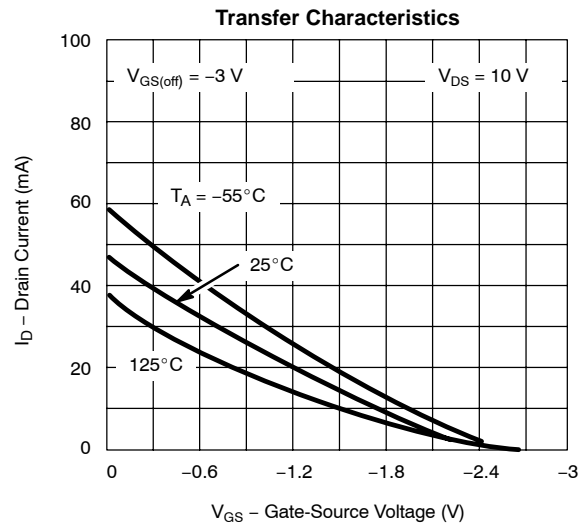
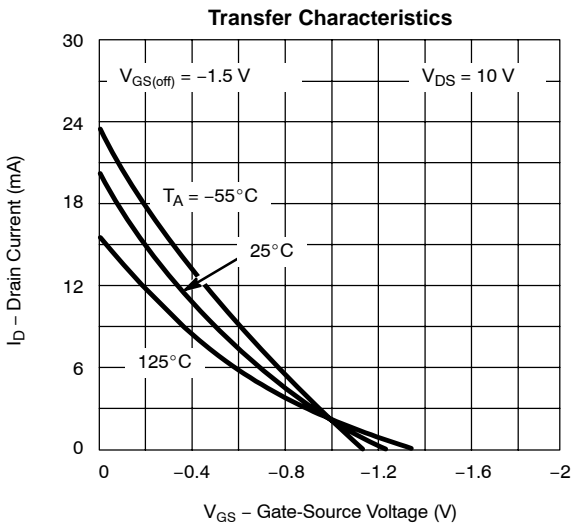
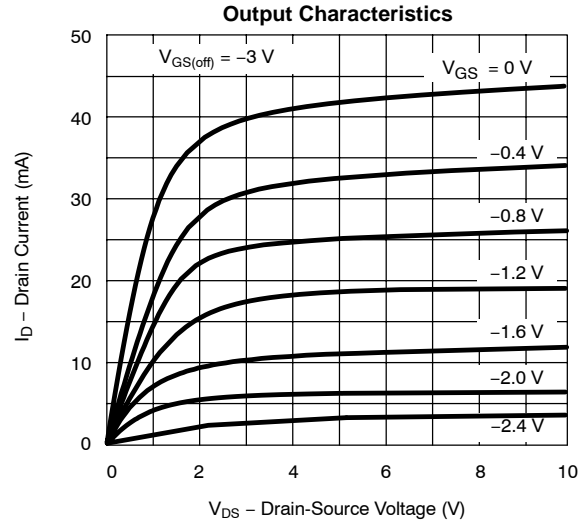
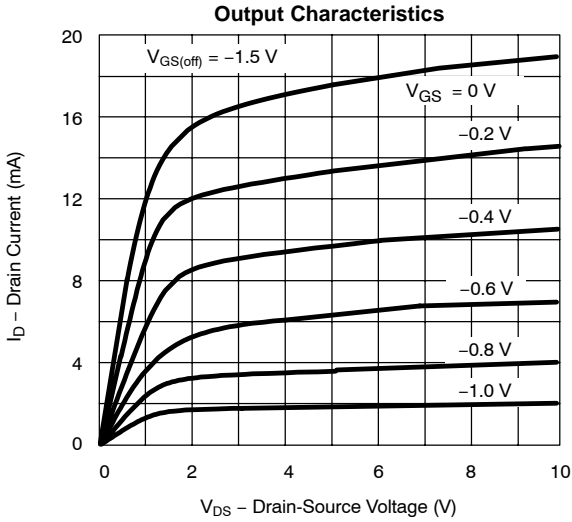
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

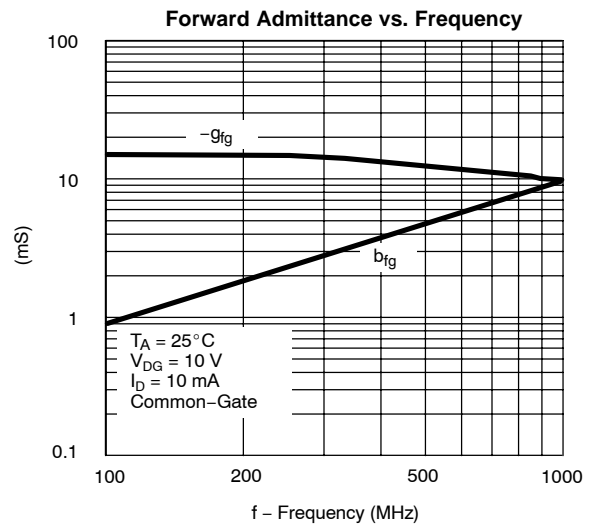
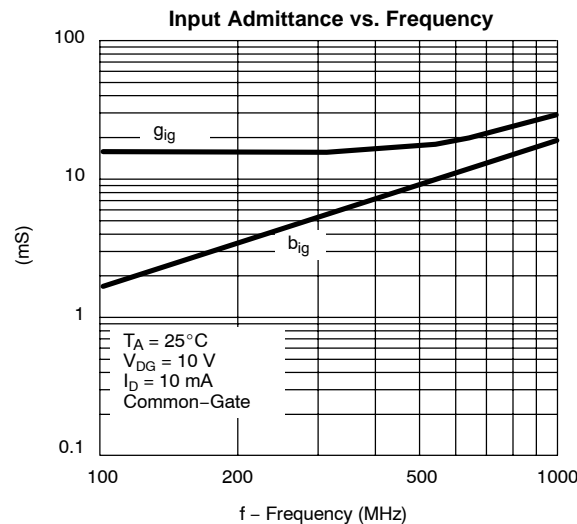
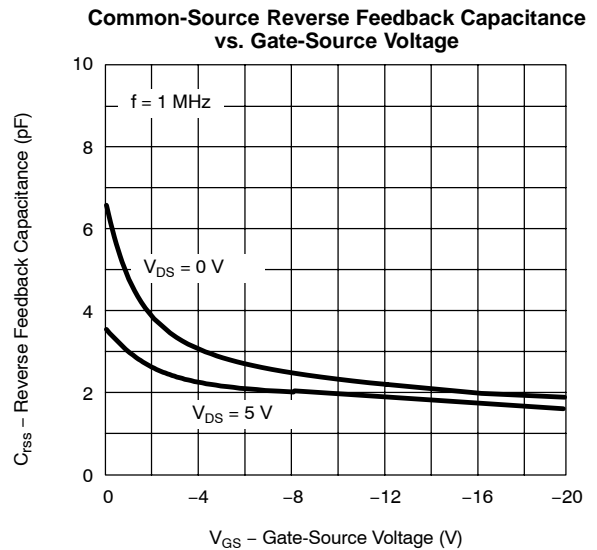
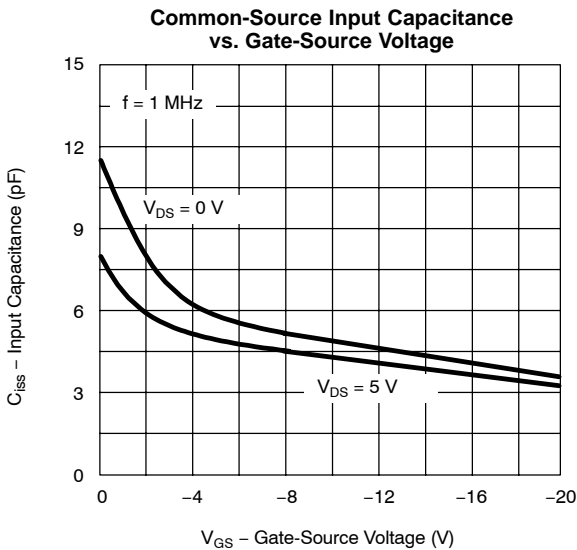
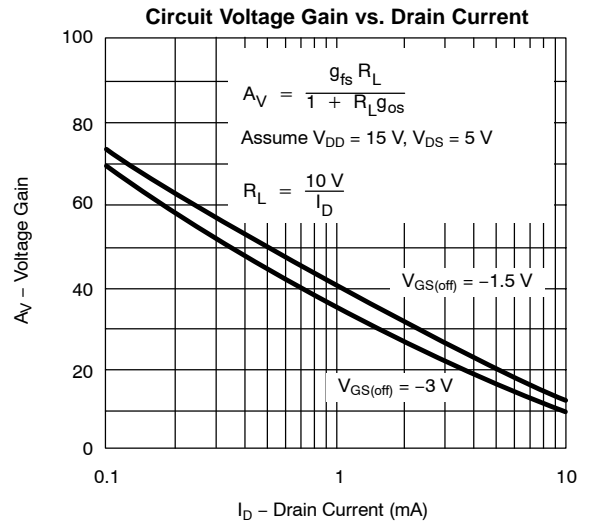
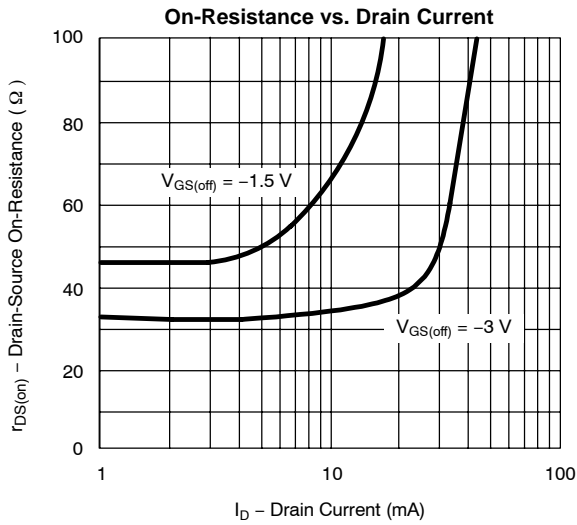




TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)



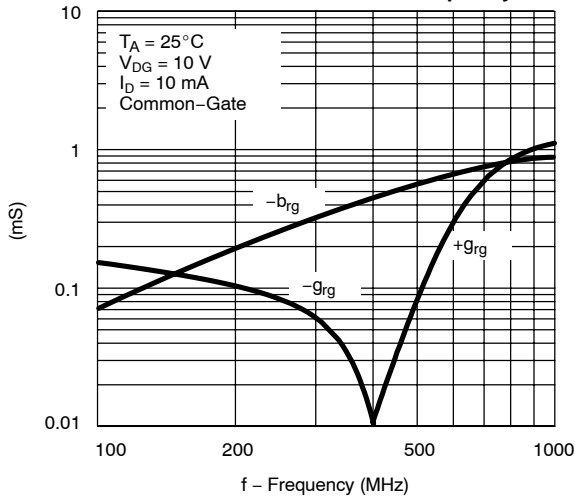
TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)



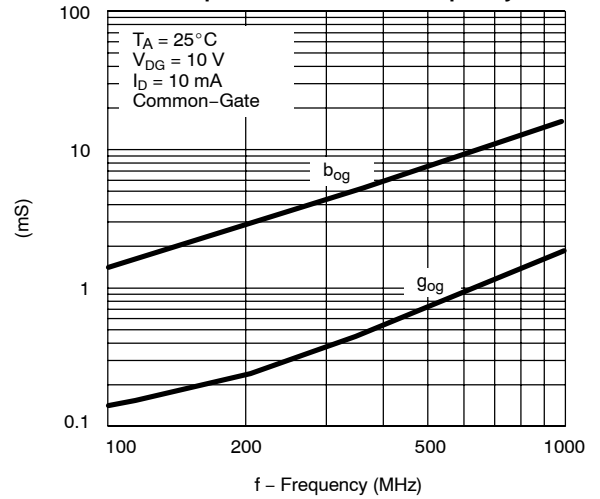


TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

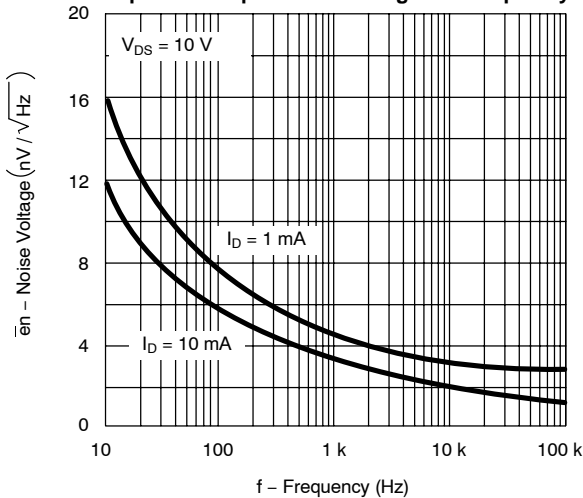
Reverse Admittance vs. Frequency



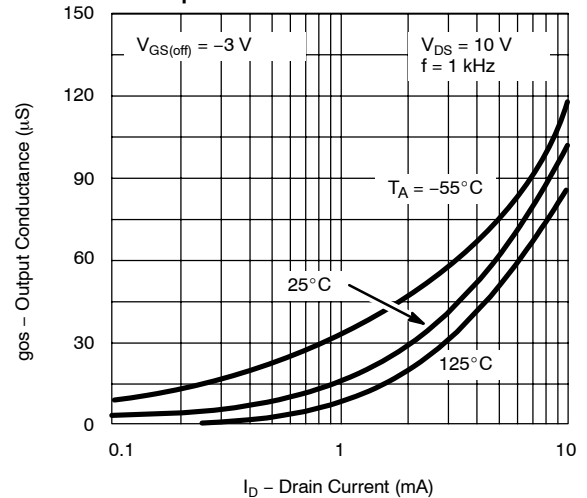
Output Admittance vs. Frequency



Equivalent Input Noise Voltage vs. Frequency



Output Conductance vs. Drain Current





Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.